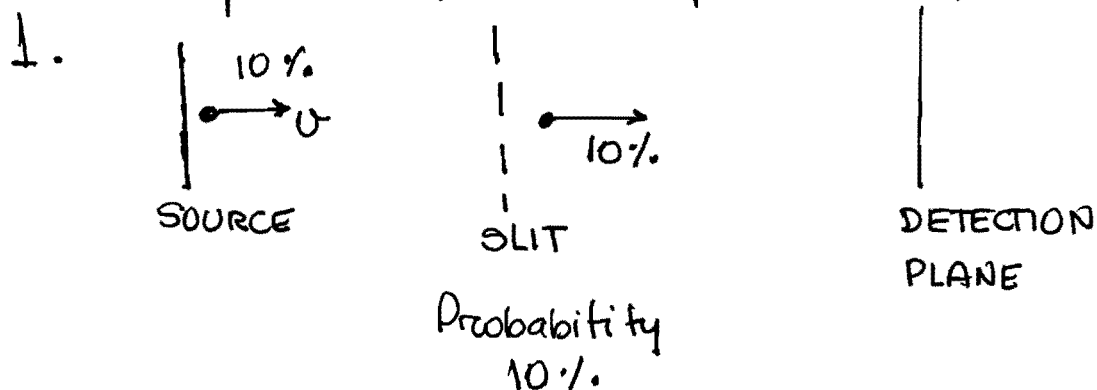


Hints on problems solution

Conceptual questions from Chapter 2



Particle is tunneling through slit -  
 Slit is invisible in Part.

If the particle makes it to the slit, then the wavefunction  $(\psi)^2 = 1$  at slit -  
 satisfies

Then there is 10% probability of the particle reaching the detector plane -

2. C3 Electrons in different states have different quantum numbers therefore can have same or different spins

Example:  $1s^1 2s^1$

$s \Rightarrow l$

$n=1$   
 $l=0$

$n=2$   
 $l=1$

How many different ways can the spins be arranged?

~~$m=0$~~   
 Spin  $\uparrow$   
 $\downarrow$

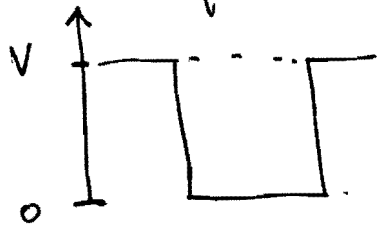
$m = 1, 0, -1$   
 $\uparrow$   
 $\downarrow$

M	1	0	-1
0	↑↑	↑↓	↑↓
0	↓↑	↓↑	↓↑

Each box - 2 arrangements

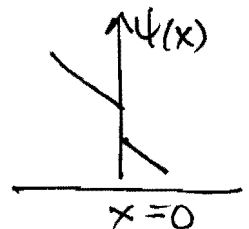
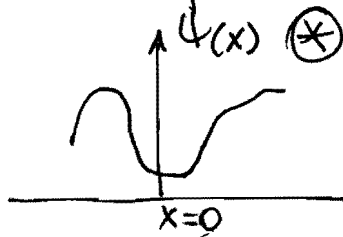
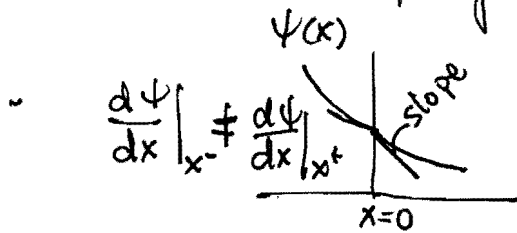
Total possibilities: 12 configurations

3. C6 Wavelength of an electron in a 1D potential for  $E = V$



The particle can either be in the well or outside the well. The state at the well/continuum interface does not have physical meaning -

4. C7 Which of the wavefunctions does not have physical meaning?



For a wavefunction to be a solution of Schrodinger's equation, it has to be continuous + its first derivative has to be continuous. The only function that satisfies this is (\*)

5 - Electrons in a crystal

Photons

$$\psi = A e^{i\vec{k}\cdot\vec{r}} e^{-iEt/\hbar}$$

$$p = \hbar k$$

$$H = E + V(\vec{r})$$

$$\psi = \vec{E} e^{i\vec{k}\cdot\vec{r}}$$

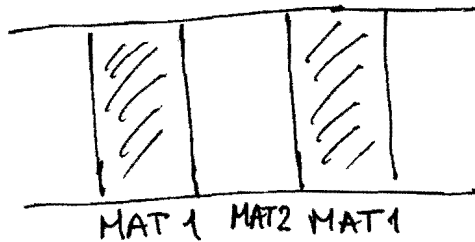
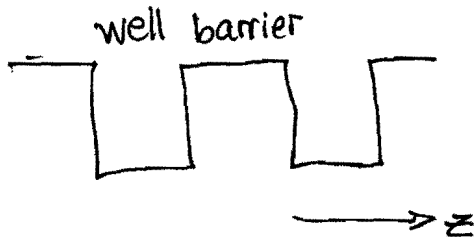
$$p = \hbar k$$

Have polarization

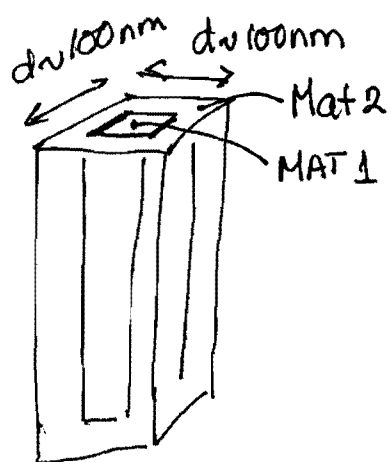
No potential in  $H$

6 - Confinement for an electron is realized by designing structures in which the potential the electron sees is discontinuous in one or more directions

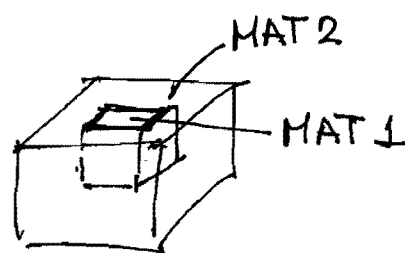
Quantum well



Bandgap Mat 1 < Bandgap Mat 2



Quantum wire  
electron confined in  
two directions



Quantum dot  
electron confined  
in three directions

### Problems

1.)  $E_{ion} = 13.6 \text{ eV}$

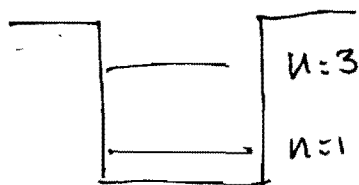
$$h\nu = E_{ion}$$

$$\frac{hc}{\lambda} = E_{ion}$$

$$\Rightarrow \nu = \frac{E_{ion}}{h}$$

$$\Rightarrow \lambda = \frac{hc}{E_{ion}}$$

2.)



Solve Schrodinger's  
equation

$$\hat{H} = \frac{\hat{p}^2}{2m}$$

obtain eigen-energies  
and eigen-functions

# Homework 2

HW # 2.1

1) Schrodinger's equation  
Crystal

$$H = \frac{p^2}{2m^*} + V(r)$$

↑  
lattice potential

$$\psi = A(r) e^{i\vec{k} \cdot \vec{r}}$$

↑  
planewaves

Hydrogen atom

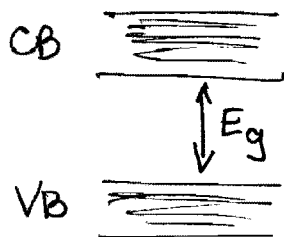
$$H = \frac{p^2}{2m} - \frac{e}{r}$$

↑  
Coulomb potential

$$\psi = R(r) Y_{lm}(\theta, \phi)$$

↑                    ↑  
polynomials    cos-like

2) - When electrons in two nearby atoms interact, the electronic structure of each of the  $e^-$  is modified. The 'new' configuration is described by two states (bonding + anti-bonding). In a crystal there are  $10^{23}$  atoms, therefore the interaction of the <sup>nearby</sup> valence electrons give rise to multiple allowed energy states. This collection of states are referred to as 'BANDS'. Top most filled band is called: VALENCE BAND. NEXT UNFILLED BAND is called: CONDUCTION BAND -

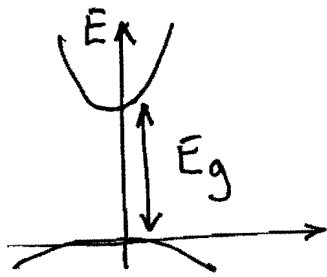


$E_g = 0$  - metal

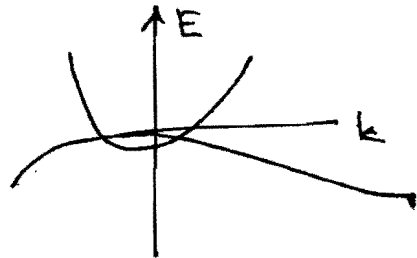
$E_g \approx 0.5 - 5$  or so eV - semiconductor

$E_g \geq 5$  eV - insulator

In terms of a band picture, in the parabolic approximation and assuming direct gap materials



SEMICONDUCTOR  
OR  
INSULATOR



METAL.

3. Hole represents the collective behavior of electrons in the valence band. When there are empty  $k$ -states, the electrons can occupy these states if there are external forces acting upon them. The motion of the empty states is opposite to that of the  $e^-$ . Therefore equivalent to a  $+e$ .

4. This problem is not phrased correctly. The density of states for CB or VB is a function. Therefore there is no meaning to calculating a value.

$$g_c(E) = \frac{1}{2\pi^2} \left( \frac{2m}{\hbar^2} \right)^{3/2} (E - E_g)^{1/2}$$

To calculate the total # of electrons/ at  $T=100K$   
 for an excess energy  $\Delta E = 60 \text{ meV}$

$$N = \int_{E_g}^{E_g + \Delta E} g_c(E) f(E) dE$$

$$\text{where } f(E) = \frac{1}{1 + \exp[(E - E_F)/k_B T]}$$

This integration is performed in the Boltzmann limit because  $\frac{E_c - E_F}{k_B T} \sim \frac{E_g}{2 k_B T} \gg 1$

$$N = N_c \exp\left[-\frac{(E_c - E_F)}{k_B T}\right] \text{ where integ from } E_g \text{ to } \infty.$$

$$\text{where } N_c = 2 \left( \frac{2\pi m_n^* k_B T}{h^2} \right)^{3/2}$$

$$\text{Ge } \frac{m_c^*}{m_0} \sim 0.55$$

$$E_c - E_F = \frac{E_g}{2}$$

$$E_F = \frac{E_g}{2}$$

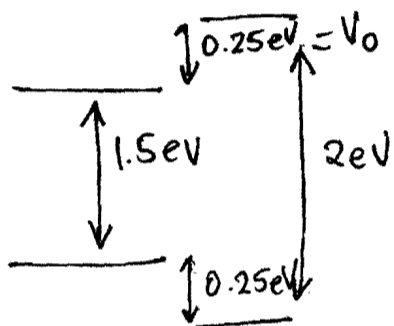
$$E_g = 0.66 \text{ eV.}$$

## HW#2 - 4

- 5 - There are many possible solutions to this problem. Need to use the semiconductor roadmap. Choose a substrate; choose well and barrier material. Well bandgap should be  $\sim 1.4 - 1.5 \text{ eV}$

Barrier bandgap  $\sim 2 \text{ eV}$   
Choose well width:  $a$

50/50 conduction/valence band split means that  $\frac{1}{2}$  of the bandgap difference is accommodated in the CB, the rest in the valence band



Energies of confined states are  

$$E_n = \frac{\hbar^2 n^2 \pi^2}{2ma^2}$$

There should be  
for 2 states  
confined

- 6 - Variation of bandgap energy in a quantum dot material with dot size.

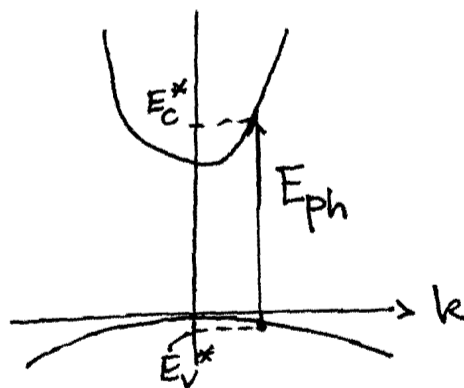
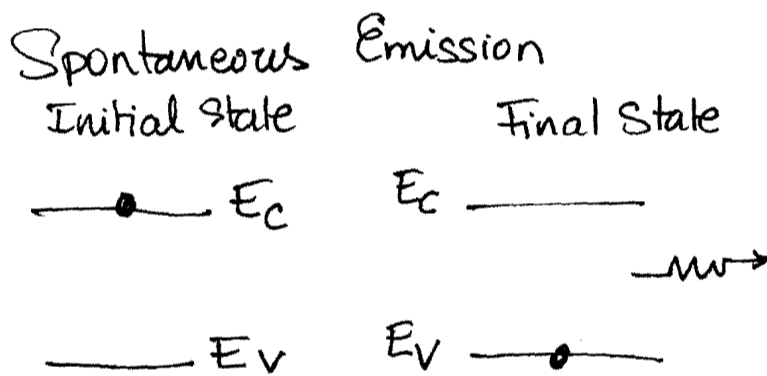
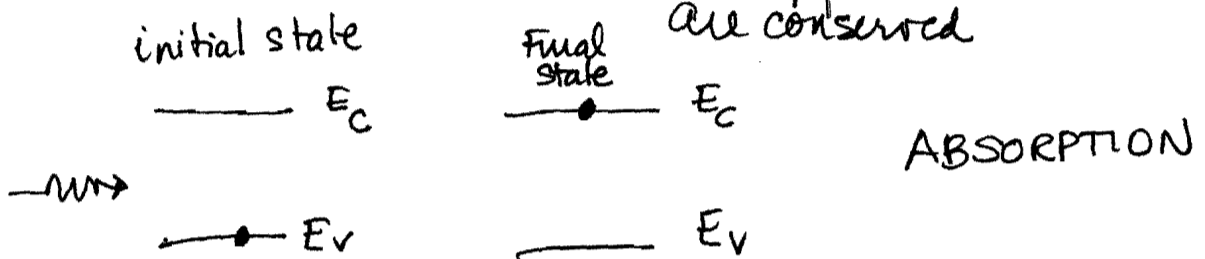
$$E = E_{\text{bandgap}} + \frac{\hbar^2 \pi^2}{2\mu a^2} \quad (\text{for CB states})$$



7. The interaction between an electron in a crystal and a photon is modelled by adding to  $H$  a term proportional to  $-\vec{A} \cdot \vec{p}$  where  $\vec{A}$  is the vector magnetic potential -

The Schrodinger equation  $H = \frac{p^2}{2m} + V(r) - \vec{A} \cdot \vec{p}$  is solved by perturbation theory.

8. Conservation laws: Energy and momentum are conserved



$k_{ph} \ll k_e$   
 Therefore an absorption transition conserves  $k$  for the electron  
 $E_V^* + E_{ph} = E_C^*$

9 - Free electron density in Na =  $2.65 \times 10^{22} / \text{cm}^3$

Calculate  $k_F$ ,  $v_F$ ,  $E_F$

$$E_F = \frac{\hbar^2 \pi^2}{2mL^2} \left( \frac{3N}{\pi} \right)^{2/3} \quad \text{for a 3D material}$$

$$L^2 = V^{2/3}$$

$$E_F = \frac{\hbar^2}{2m} \left( \frac{3\pi^2 N}{V} \right)^{2/3}$$

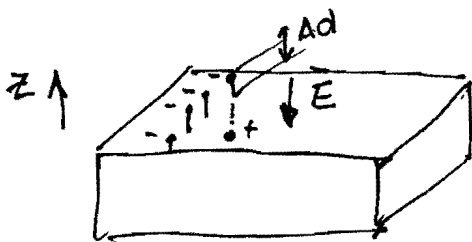
$\frac{N}{V} =$  # electrons per unit volume -

$$k_F \text{ is obtained from } \rightarrow E_F = \frac{\hbar^2 k_F^2}{2m_0}$$

$$v_F \text{ is obtained from } p = \hbar k_F = m v_F$$

Fermi Energy is related to pop of electrons in a system; variations in  $E_F$  represent variations in  $N$ .

#### 10 - Exercise 4



$$E \propto E_0 e^{i\omega t}$$

Charge density  $n$   
motion of displaced charge

$$F = ma$$

$$-eEz = m \frac{d^2 z}{dt^2}$$

← harmonic oscillator

$$\omega = \sqrt{\frac{k}{m}}$$

## 11 - Exercise #8

Charging energy of  
Fe atom ( $r = 1.25 \text{ \AA}$ )  
100 nm - QD -

$$\Delta V = \frac{e}{8\pi\epsilon\epsilon_0 a} \text{ Volts}$$

$a = \text{radius} -$